

InAsSb photodiode

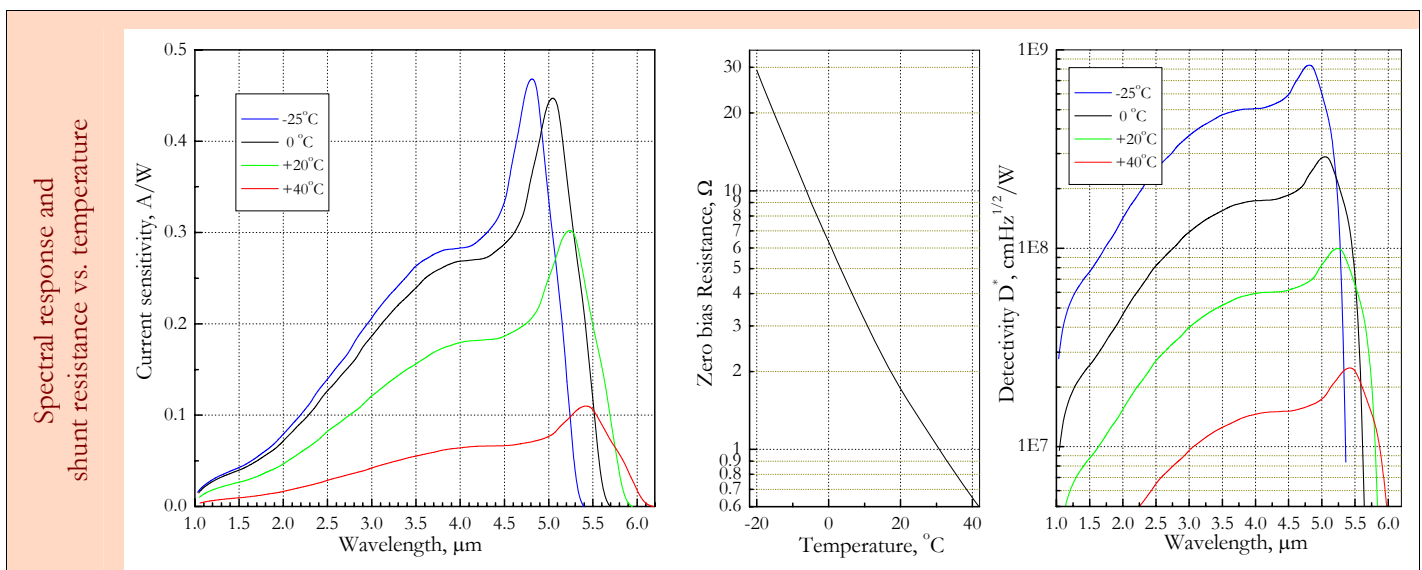
PD53fsi series

Peak wavelength	λ	μm	5.2 ± 0.1
Spectral response range	$\lambda_{0.1}$	μm	$1.8 \div 5.8$
Current sensitivity	S_I	A/W	≥ 0.3
Resistance at zero bias	R_0	Ohm	≥ 1.5
Detectivity	$D^*_{\lambda_{\text{max}}}$	$\text{cmHz}^{1/2}\text{W}^{-1}$	$\geq 1 \times 10^8$
Voltage sensitivity	S_U	V/W	≥ 0.45
Switching time	τ	ns	$< 50^*$

* - according estimation

Model	Package	Cap with window	Sensitive area, mm	Angle of view FWHM, deg.	Operation conditions, °C	Polarity
PD53fsiTO18	TO18 (TO46)	-		140		
PD53fsiTO18c	TO18 (TO46)	Sapphire	0.33x0.33	50	-25÷+60	Short leg is negative
PD53fsiTO39c	TO39	Sapphire		90		

	PD53fsiTO18	PD53fsiTO18c	PD53fsiTO39c
Product view			
Features	Growth of narrow gap semiconductor alloys onto n ⁺ -InAs substrate; "Wide gap" window	Ambient and high temperature operation; No bias required; Short time constant; Operation from DC to VHF; Highest long term stability	
<p>Data are valid for 22°C. Photodiode could be equipped with preamplifier that is designed for conversion of PD photocurrent into a convenient output voltage and is adjusted for the particular PD taking into account the R₀ value and frequency range. Other packages are available upon request</p>			



Product specifications are subject to change without prior notice due to improvements or other reasons. Updated 14.10.11



ООО «Июффе ЛЕД»
Ioffe LED, Ltd

Politechnicheskaya 26,
 St.Petersburg, 194021, RUSSIA

<http://www.ioffeled.com>
 e-mail: Mremenny@mail.ioffe.ru
 Tel./fax: +7 812 297 7446